**Preferred Device** 

# **Triacs**

# **Silicon Bidirectional Thyristors**

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

#### **Features**

- Blocking Voltage to 800 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC15 Series) or Four Modes (MAC15A Series)
- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage Note 1 $(T_J = -40 \text{ to } +125^{\circ}\text{C}, \text{ Sine Wave } 50 \text{ to } 60 \text{ Hz}, \text{Gate Open})$	V <sub>DRM,</sub> V <sub>RRM</sub>	400 600 800	٧
Peak Gate Voltage (Pulse Width $\leq 1.0 \mu sec; T_C = 90^{\circ}C$ )	$V_{GM}$	10	V
On–State Current RMS; Full Cycle Sine Wave 50 to 60 Hz (T <sub>C</sub> = +90°C)	I <sub>T(RMS)</sub>	15	Α
Circuit Fusing Consideration (t = 8.3 ms)	l <sup>2</sup> t	93	A <sup>2</sup> s
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = +80°C) Preceded and Followed by Rated Current	I <sub>TSM</sub>	150	Α
Peak Gate Power (T <sub>C</sub> = +80°C, Pulse Width = 1.0 μs)	P <sub>GM</sub>	20	W
Average Gate Power (T <sub>C</sub> = +80°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.5	W
Peak Gate Current (Pulse Width $\leq 1.0 \mu sec; T_C = 90^{\circ}C$ )	I <sub>GM</sub>	2.0	Α
Operating Junction Temperature Range	$T_J$	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



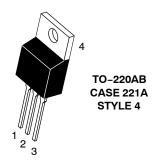
#### ON Semiconductor®

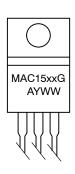
http://onsemi.com

# TRIACS 15 AMPERES RMS 400 thru 800 VOLTS



#### MARKING DIAGRAM





MAC15xx = Specific Device Code xx = See Table on Page 2 A = Assembly Location Y = Year WW = Work Week

= Pb-Free Package

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	2.0	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T <sub>L</sub>	260	°C

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		•	
Peak Blocking Current (V <sub>D</sub> = Rated V <sub>DRM</sub> , V <sub>RRM</sub> ; Gate Open)	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C	I <sub>DRM,</sub> I <sub>RRM</sub>		- -	10 2.0	μA mA
ON CHARACTERISTICS				ı	ul	I
Peak On-State Voltage Note 2 (I <sub>TM</sub> = ±21 A Peak)		$V_{TM}$	-	1.3	1.6	V
Gate Trigger Current (Continuous dc) ( $V_D$ = 12 Vdc, $R_L$ = 100 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY		l <sub>GT</sub>	- - - -	- - - -	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) ( $V_D$ = 12 Vdc, $R_L$ = 100 $\Omega$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY		V <sub>GT</sub>	- - - -	0.9 0.9 1.1 1.4	2 2 2 2.5	V
Gate Non–Trigger Voltage ( $V_D$ = 12 V, $R_L$ = 100 $\Omega$ ) $T_J$ = 110°C) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY			0.2 0.2	- -	- -	V
Holding Current (V <sub>D</sub> = 12 Vdc, Gate Open, Initiating Current = ±200 mA)			-	6.0	40	mA
Turn-On Time ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 17 A) ( $I_{GT}$ = 120 mA, Rise Time = 0.1 $\mu$ s, Pulse Width = 2 $\mu$ s)			-	1.5	-	μs
DYNAMIC CHARACTERISTICS			•	•	•	
Critical Rate of Rise of Commutation Voltage ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 21 A, Commutating di/dt = 7.6 A/ms, Gate Unenergized, $T_C$ = 80°C)			-	5.0	_	V/μs

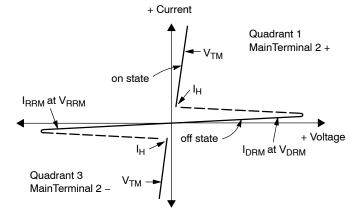
<sup>2.</sup> Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

#### **ORDERING INFORMATION**

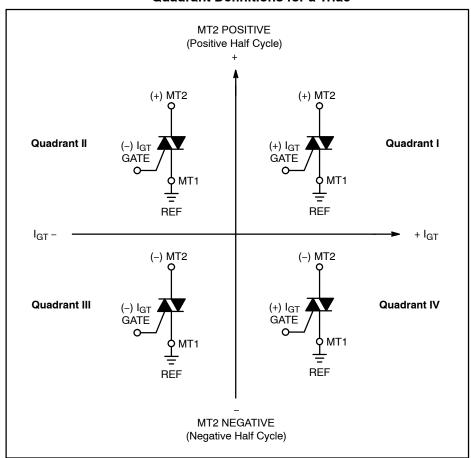
Device	Device Marking	Package	Shipping
MAC15-008		TO-220AB	
MAC15-8G	MAC15-8	TO-220AB (Pb-Free)	
MAC15-10		TO-220AB	
MAC15-10G	MAC1510	TO-220AB (Pb-Free)	
MAC15A6		TO-220AB	
MAC15A6G	MAC15A6	TO-220AB (Pb-Free)	500 Units Bulk
MAC15A8		TO-220AB	
MAC15A8G	MAC15A8	TO-220AB (Pb-Free)	
MAC15A10		TO-220AB	
MAC15A10G	MAC15A10	TO-220AB (Pb-Free)	
MAC15A10T		TO-220AB	50 Units / Rail

# Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current



#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

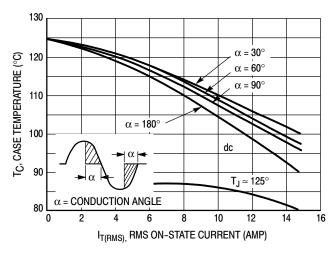


Figure 1. RMS Current Derating

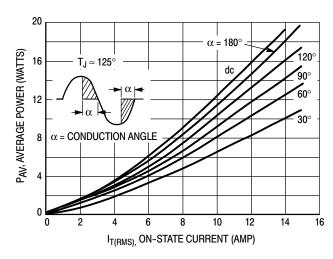


Figure 2. On-State Power Dissipation

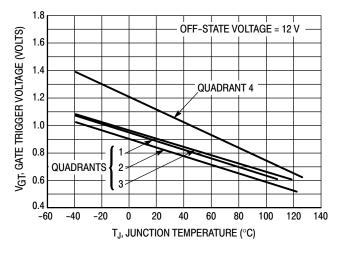


Figure 3. Typical Gate Trigger Voltage

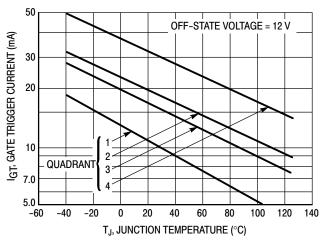
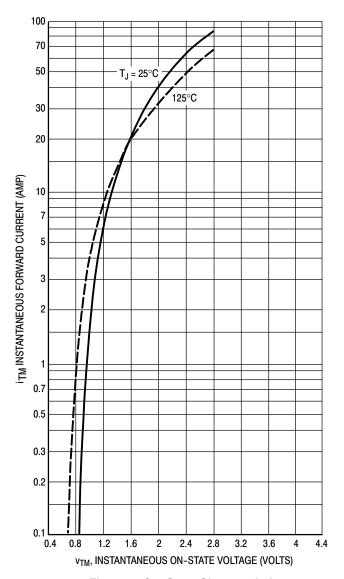


Figure 4. Typical Gate Trigger Current



20 GATE OPEN MAIN TERMINAL #1 **POSITIVE** IH, HOLDING CURRENT (mA) 10 7.0 5.0 MAIN TERMINAL #2 **POSITIVE** 3.0 2.0 -40 80 -60 -20 20 40 60 100 120 140 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 6. Typical Holding Current

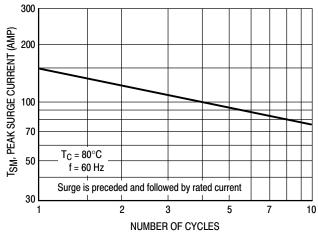


Figure 5. On-State Characteristics

Figure 7. Maximum Non-Repetitive Surge Current

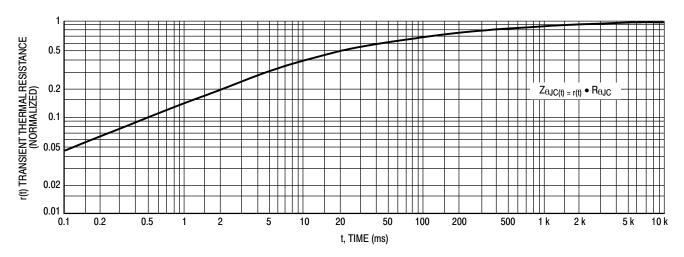
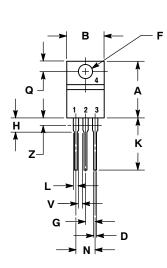
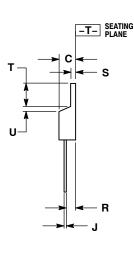


Figure 8. Thermal Response

#### PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 **ISSUE O** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL
  BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 4:

PIN 1. MAIN TERMINAL 1

MAIN TERMINAL 2 2.

GATE

MAIN TERMINAL 2

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